Product data sheet

1. General description

Dual Silicon Carbide Schottky diode in a TO247 plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- · Highly stable switching performance
- · Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Notes | | Values | | Unit |
|--------------------|----------------------------------|--|-------|------------|--------|------|------|
| Absolute | maximum rating | | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | | | 650 | | V |
| I _{O(AV)} | limiting average forward current | δ = 0.5; square-wave pulse; $T_{mb} \le 114$ °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3 | | 20 | | А | |
| T _j | junction temperature | | | -55 to 175 | | °C | |
| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit |
| Static ch | aracteristics | | | | | | |
| V_{F} | forward voltage | I _F = 10 A; T _j = 25 °C; per diode; <u>Fig. 5</u> | | - | 1.45 | 1.70 | V |
| | | I _F = 10 A; T _j = 150 °C; per diode; <u>Fig. 5</u> | | - | 1.80 | 2.20 | V |
| Dynamic | characteristics | | | | | | |
| Q_r | recovered charge | $I_F = 10 \text{ A}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; $V_R = 400 \text{ V}$; $T_j = 25 ^{\circ}\text{C}$; per diode; Fig. 7 | | - | 14.5 | - | nC |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------------------|--------------------|----------------|
| 1 | A1 | anode | | |
| 2 | K | cathode | | A1 |
| 3 | A2 | anode | | K |
| mb | mb | mounting base; connected to cathode | 1 2 3 | sym125 |

6. Ordering information

Table 3. Ordering information

| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|---------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| WNSC5D20650CW | TO247 | WNSC5D20650CW6Q | Tube | 30 | TO247N | 20-July-2016 |

7. Marking

Table 4. Marking codes

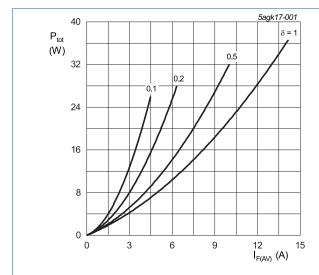
| Type number | Marking codes |
|---------------|-------------------|
| WNSC5D20650CW | WNSC5D 20650CW |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Notes | Values | Unit |
|--------------------|--|--|-------|------------|------------------|
| V_{RRM} | repetitive peak reverse voltage | | | 650 | V |
| V_{RWM} | crest working reverse voltage | | | 650 | V |
| V_R | reverse voltage | DC | | 650 | V |
| I _{O(AV)} | limiting average forward current | δ = 0.5; square-wave pulse; T _{mb} ≤ 114 °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u> | | 20 | А |
| I _{FRM} | repetitive peak forward current | δ = 0.5; t _p = 25 μs; T _{mb} ≤ 119 °C; square-wave pulse; per diode | | 20 | А |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode | | 60 | А |
| | | t_p = 10 μ s; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode | | 540 | А |
| l ² t | I ² t for fusing | sine-wave pulse; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$ | | 18 | A ² s |
| T _{stg} | storage temperature | | | -55 to 175 | °C |
| T _j | junction temperature | | | -55 to 175 | °C |



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_o = 1.103 \text{ V; } R_s = 0.1048 \text{ }\Omega$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

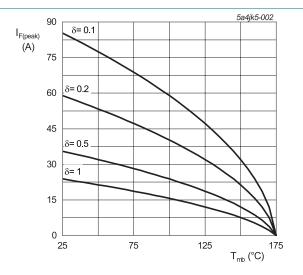
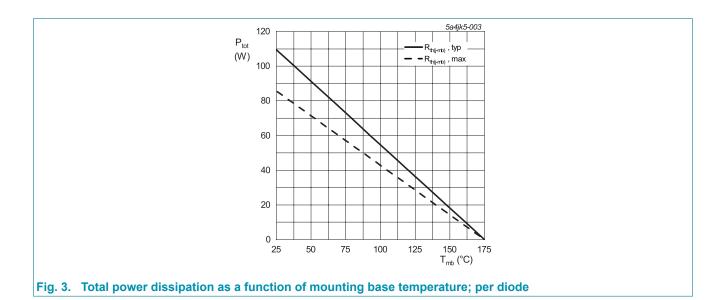


Fig. 2. Current derating as a function of mounting base temperature; per diode



9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit |
|-----------------------|--|------------------------|-------|-----|------|------|------|
| R _{th(j-mb)} | thermal resistance | per diode; Fig. 4 | | - | 1.37 | 1.75 | K/W |
| | from junction to mounting base | both diodes conducting | | - | 0.75 | 0.95 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient free air | in free air | | - | 60 | - | K/W |

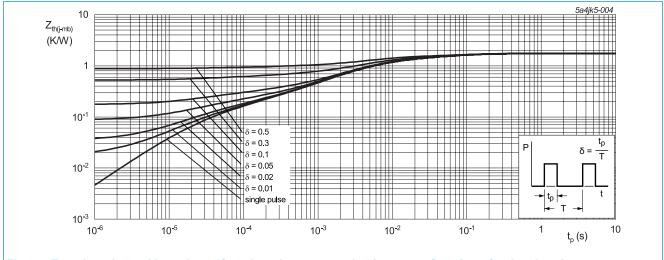
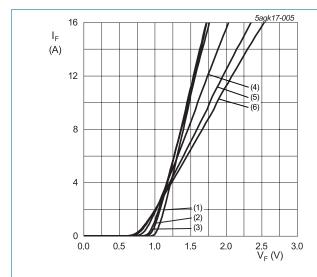


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7 Characteristics

| Table 7. O | iaracteristics | | | | | | |
|-----------------|---------------------------------|---|-------|-----|------|------|------|
| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | | |
| V_{F} | forward current | I _F = 10 A; T _j = 25 °C; per diode; <u>Fig. 5</u> | | - | 1.45 | 1.70 | V |
| | | I _F = 10 A; T _j = 150 °C; per diode; <u>Fig. 5</u> | | - | 1.80 | 2.20 | V |
| | | I _F = 10 A; T _j = 175 °C; per diode; <u>Fig. 5</u> | | - | 2.00 | 2.30 | V |
| I _R | reverse current | $V_R = 650 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}; Fig. 6$ | | - | 0.5 | 50 | μΑ |
| | | V _R = 650 V; T _j = 175 °C; per diode; <u>Fig. 6</u> | | - | 25 | 250 | μA |
| Dynamic | characteristics | | | | | | |
| Q_r | recovered charge | $I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; per diode; Fig. 7$ | | - | 14.5 | - | nC |
| C _d | diode capacitance | $f = 1 \text{ MHz}$; $V_R = 1 \text{ V}$; $T_j = 25 \text{ °C}$; per diode | | - | 328 | - | pF |
| | | $f = 1 \text{ MHz; } V_R = 300 \text{ V; } T_j = 25 \text{ °C; per diode}$ | | - | 39 | - | pF |
| | | $f = 1 \text{ MHz}$; $V_R = 600 \text{ V}$; $T_j = 25 \text{ °C}$; per diode | | - | 36 | - | pF |
| E _{as} | non-repetitive avalanche energy | $I_R = 4.9 \text{ A}$; L = 5 mH; $T_{\text{j(init)}} = 25 ^{\circ}\text{C}$; per diode | | 60 | - | - | mJ |



 V_o = 1.103 V; R_s = 0.1048 Ω

(1) $T_j = -55$ °C; typical values

(2) T_j = 0 °C; typical values

(3) T_i = 25 °C; typical values

(4) $T_j = 100 \, ^{\circ}\text{C}$; typical values

(5) $T_j = 150$ °C; typical values

(6) T_i = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values; per diode

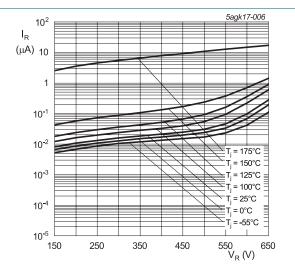


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

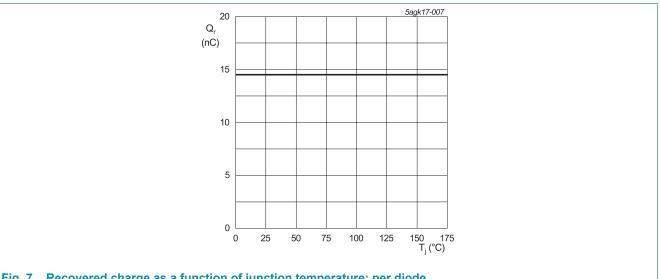
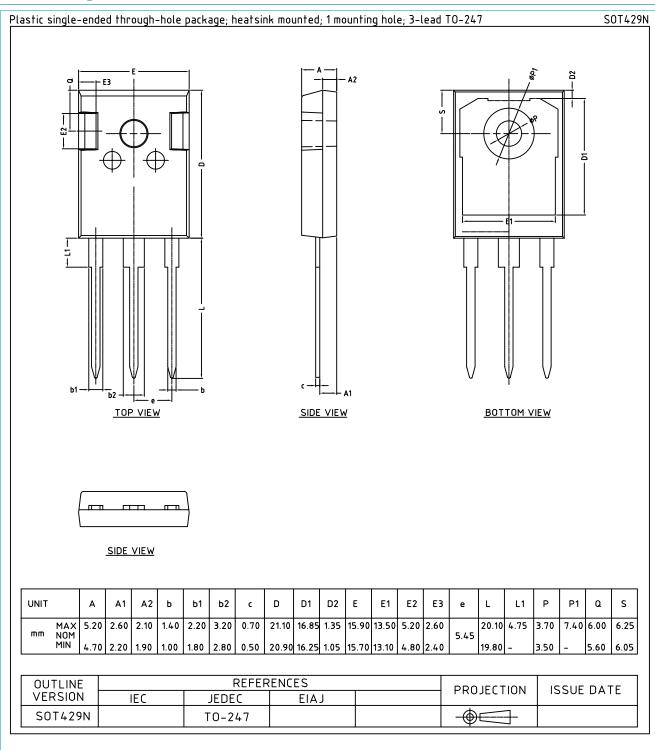


Fig. 7. Recovered charge as a function of junction temperature; per diode

11. Package outline



12. Legal information

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|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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